

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|---|------------------|---------|---------------------|
| S1 | 37 | gate same (ild or (interlayer adj dielectric)) same coplanar | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 09:44 |
| S2 | 13 | gate same (ild or (interlayer adj dielectric)) same ("same" adj plane) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 09:47 |
| S3 | 19 | gate same (ild or (interlayer adj dielectric)) same ("same" adj level) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 09:48 |
| S4 | 31 | gate same (ild or (interlayer adj dielectric)) same ("same" adj height) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 09:54 |
| S5 | 1 | gate same (ild or (interlayer adj dielectric)) same ("same" adj altitude) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 10:08 |
| S6 | 0 | gate same (ild or (interlayer adj dielectric)) same ("same" adj tallness) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 10:10 |
| S7 | 0 | gate same (ild or (interlayer adj dielectric)) same ("same" adj stature) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 10:10 |

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|-----|-----|---|---|----|----|---------------------|
| S8 | 2 | gate same (ild or (interlayer adj dielectric)) same ("same" adj elevation) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 10:10 |
| S9 | 0 | gate same (ild or (interlayer adj dielectric)) same ("same" adj (pinnacle or summit or peak or top or apex or acme or zenith or loftiness)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 10:13 |
| S10 | 0 | gate same (ild or (interlayer adj dielectric)) same (conductor near (metal adj silicide)) same (polysilicon or (polycrystalline adj (si or silicon))) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 12:26 |
| S11 | 268 | gate same (ild or (interlayer adj dielectric)) same (conductor near\$2 (metal adj silicide)) same (polysilicon or (polycrystalline adj (si or silicon))) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 12:27 |
| S12 | 695 | gate same (ild or (interlayer adj dielectric)) same (conduct\$3 near\$2 (metal adj silicide)) same (polysilicon or (polycrystalline adj (si or silicon))) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 12:27 |
| S13 | 0 | gate same (ild or (interlayer adj dielectric)) same (conduct\$3 adj (coupled or connected) adj (metal adj silicide)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 13:43 |

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| S14 | 0 | gate same (ild or (interlayer adj dielectric)) same ((conduct\$3 adj (layer or film)) adj (coupled or connected) adj (metal adj silicide)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 13:44 |
| S15 | 0 | ((conduct\$3 adj (layer or film)) adj (coupled or connected) adj (metal adj silicide)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 13:44 |
| S16 | 0 | ((conduct\$3 adj (layer or film)) near (coupled or connected) near (metal adj silicide)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 14:04 |
| S17 | 116 | ((conduct\$3 adj (layer or film)) with (coupled or connected) with (metal adj silicide)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 14:05 |
| S18 | 455 | ((conduct\$3 adj (layer or film)) same (coupled or connected) same (metal adj silicide)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/18 14:08 |

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